

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	9	("20030068134" "5033812" "5101549" "5132843" "5436991" "5659640" "5742433" "6285813" "6788847").PN.	US-PGPUB; USPAT	OR	ON	2005/09/07 19:36
S2	5	"182262".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/06 14:32
S3	5	"606297".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/06 14:32
S4	9	("20030068134" "5033812" "5101549" "5132843" "5436991" "5659640" "5742433" "6285813" "6788847").PN.	US-PGPUB; USPAT	OR	ON	2005/09/07 09:58
S5	1	S4 and salicide	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 10:06
S6	2	S4 and (light near scatter\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 10:07
S7	1	S5 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 10:57
S8	33	(core strip waveguid\$3) near7 ("same" near7 (layer level)) near7 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:09
S9	428	clad\$4 near7 (salicide (silicon. near3 nitride) SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:04
S10	8	S8 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:43
S11	235	(core strip waveguid\$3) near7 "same" near7 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:10
S12	17	S9 and S11	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:21

S13	217834	(slab layer) near4 silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:49
S14	242936	(slab layer) near7 (dielectric clad\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:51
S15	355	(waveguid\$3 strip core) near7 transistor near7 "same"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:57
S16	8696	(gate near3 oxide) near7 (dielectric clad\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:52
S17	14801	(polysilicon) near7 (dielectric clad\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:51
S18	6957	(gate near3 polysilicon) near7 (transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:52
S19	385	clad\$4 near7 (salicide (silicon near2 nitride) SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:48
S20	0	S13 and S14 and S15 and S16 and S17 and S18 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:43
S21	163	S13 and S14 and S15	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:56
S22	17	S15 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 12:10
S23	17	S21 and S22	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 11:56
S24	5	"177002".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 12:28

S26	0	S15 and S16 and S17 and S18 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:44
S27	9	S15 and S17 and S18 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:44
S28	2	S15 and S16 and S18 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:44
S29	2	S15 and S16 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:44
S30	7	S15 and S16 and S18	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:47
S31	7901	385/2,14,40,129-132.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:47
S32	106	S31 and ((waveguid\$3 strip core) near7 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:48
S33	71	S31 and (clad\$4 near7 (salicide (silicon near2 nitride) SiN))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:49
S34	15	S32 and S33	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:51
S38	6107	(waveguid\$3 strip core) near7 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:57
S39	21	S19 and S38	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 13:58
S40	245145	(slab layer) near6 silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:04

S41	194415	dielectric near5 (slab layer silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:04
S42	5451	strip near5 silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:05
S43	2433	strip near9 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:06
S44	10159	strip near6 dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:06
S45	35877	gate near7 dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:06
S46	14712	polysilicon near7 dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:06
S47	23	S40 and S41 and S42 and S43 and S44 and S45 and S46	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:07
S48	4	S40 and S41 and S42 and S43 and S44 and S45 and S46 and clad\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:07
S49	4	S48 and (salicide (silicon adj nitride) SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 15:57
S50	35	(strip core) near5 "same" near5 (material layer level time) near8 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:14
S51	68	(light near3 scatter\$3) and (dielectric near4 strip)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:15
S52	4880	dielectric near7 (gate adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:16

S53	14712	dielectric near7 polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:16
S54	374	clad\$ near7 (salicide (silicon adj nitride) SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:16
S55	0	S51 and S52 and S53 and S54	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:17
S56	2	S51 and S54	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:17

S57	79	("20020094183"   "20020164118"   "20020164129"   "20020164143"   "20030031446"   "20040076362"   "3462211"   "3970364"   "3976358"   "4420873"   "4776655"   "4787691"   "4857973"   "4877299"   "4956682"   "4958898"   "4999686"   "5001523"   "5003359"   "5033812"   "5048907"   "5061030"   "5078516"   "5101459"   "5109464"   "5125065"   "5132843"   "5146513"   "5148507"   "5200939"   "5222162"   "5225740"   "5303319"   "5314107"   "5329601"   "5347601"   "5436991"   "5459807"   "5534824"   "5546494"   "5625725"   "5654818"   "5682455"   "5684817"   "5703989"   "5737474"   "5742433"   "5745630"   "5759453"   "5784400"   "5841931"   "5889898"   "5908305"   "5917981"   "5955749"   "6052495"   "6055342"   "6101300"   "6108464"   "6134369"   "6151430"   "6175671"   "6195187"   "6229947"   "6243517"   "6261525"   "6278822"   "6285813"   "6374001"   "6396984"   "6400490"   "6411752"   "6466342"   "6507681"   "6614977"   "6636668"   "6734453"   "6759675").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/07 14:24
S58	7	S57 and (transistor near7 (core strip waveguid\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 14:27
S59	62	(slab near4 silicon) same (dielectric (silicon near2 diodixe) SiO2)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 15:50
S60	10970	strip near7 (dielectric (silicon near2 diodixe) SiO2)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 15:55

S61	2619	strip near10 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 15:55
S62	193155	(light near2 scatter\$3) grating	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 15:56
S63	8	S59 and S60 and S61 and S62	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 15:55
S64	403	((light near2 scatter\$3) grating) and (transistor same waveguide)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 15:56
S65	372	clad\$4 near7 (salicide (silicon adj nitride) SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 17:48
S66	24	S64 and S65	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 15:57
S68	0	((slab layer) near3 silicon) and (dielectric clad\$4) and strip and transistor and (scatter\$3 grating) and gate and polysilicon and (clad\$4 near4 (salicide (silicon adj nitride) SiN))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/07 19:37
S69	8368	(core near5 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/08 11:26
S70	61	(core waveguide) with transistor with ("same" near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/08 11:01
S71	269	clad\$4 near5 (salicide (silicon adj nitride) SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/08 11:01
S72	8	S69 and S70 and S71	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/08 11:08
S73	17	S70 and S71	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/08 11:08

S74	9	S73 not S72	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/08 11:08
S78	0	((core and silicon) and transistor and (clad\$4 near5 (salicide (silicon adj nitride) SiN))).clm.	US-PGPUB	OR	ON	2005/09/08 11:30



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L1	0	((core and silicon) and transistor and (clad\$4 near5 (salicide (silicon adj nitride) SiN))).clm.	US-PGPUB	OR	ON	2005/09/08 11:30